

DATA SHEET

BUT18; BUT18A Silicon diffused power transistors

Product specification
Supersedes data of 1997 Aug 13

1999 Jun 11

Silicon diffused power transistors

BUT18; BUT18A

DESCRIPTION

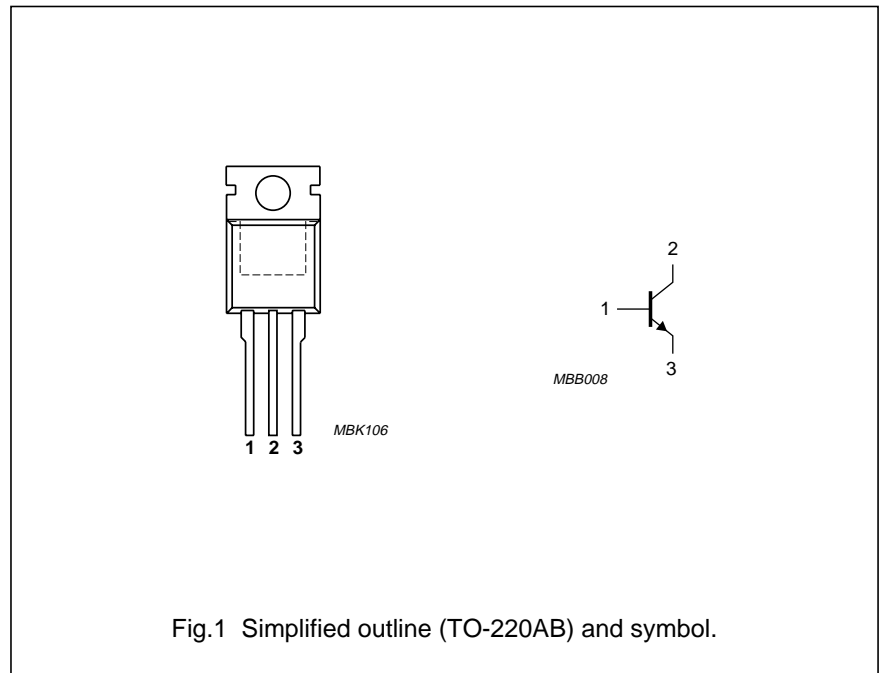
High-voltage, high-speed, glass-passivated NPN power transistor in a TO-220AB package.

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor control systems.

PINNING

PIN	DESCRIPTION
1	base
2	collector; connected to mounting base
3	emitter



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0$	850	V
	BUT18			
V_{CEO}	collector-emitter voltage	open base	400	V
	BUT18A			
V_{CEsat}	collector-emitter saturation voltage	see Fig.7	1.5	V
I_{Csat}	collector saturation current		4	A
I_C	collector current (DC)	see Fig.2	6	A
I_{CM}	collector current (peak value)	see Fig.2	12	A
P_{tot}	total power dissipation	$T_{mb} \leq 25\text{ }^\circ\text{C}$; see Fig.4	110	W
t_f	fall time	resistive load; see Figs 10 and 11	0.8	μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	1.15	K/W

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0$	–	850	V
	BUT18 BUT18A			1000	V
V_{CEO}	collector-emitter voltage	open base	–	400	V
	BUT18 BUT18A			450	V
I_{Csat}	collector saturation current		–	4	A
I_C	collector current (DC)	see Fig.2	–	6	A
I_{CM}	collector current (peak value)	see Fig.2	–	12	A
I_B	base current (DC)		–	3	A
I_{BM}	base current (peak value)		–	6	A
P_{tot}	total power dissipation	$T_{mb} \leq 25\text{ °C}$; see Fig.4	–	110	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified.

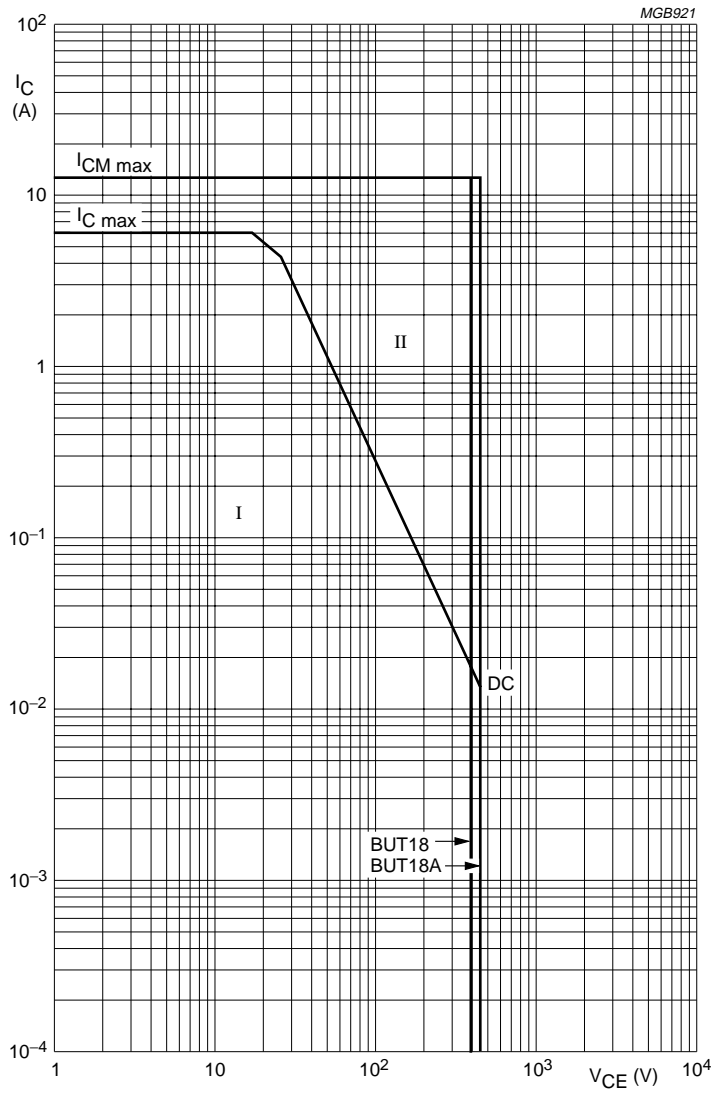
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{CEO_{sust}}$	collector-emitter sustaining voltage	$I_C = 0.1\text{ A}$; $I_{Boff} = 0$; $L = 25\text{ mH}$; see Figs 5 and 6	400 450	–	–	V
	BUT18 BUT18A				–	V
V_{CEsat}	collector-emitter saturation voltage	$I_C = 4\text{ A}$; $I_B = 0.8\text{ A}$; see Fig.7	–	–	1.5	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 4\text{ A}$; $I_B = 0.8\text{ A}$; see Fig.8	–	–	1.3	V
I_{CES}	collector-emitter cut-off current	$V_{CE} = V_{CESM_{max}}$; $V_{BE} = 0$; note 1	–	–	1	mA
		$V_{CE} = V_{CESM_{max}}$; $V_{BE} = 0$; $T_j = 125\text{ °C}$; note 1	–	–	2	mA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 9\text{ V}$; $I_C = 0$	–	–	10	mA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}$; $I_C = 10\text{ mA}$; see Fig.9	10	18	35	
		$V_{CE} = 5\text{ V}$; $I_C = 1\text{ A}$; see Fig.9	10	20	35	
Switching times resistive load (see Figs 10 and 11)						
t_{on}	turn-on time	$I_{Con} = 4\text{ A}$; $I_{Bon} = -I_{Boff} = 800\text{ mA}$	–	–	1	μs
t_s	storage time	$I_{Con} = 4\text{ A}$; $I_{Bon} = -I_{Boff} = 800\text{ mA}$	–	–	4	μs
t_f	fall time	$I_{Con} = 4\text{ A}$; $I_{Bon} = -I_{Boff} = 800\text{ mA}$	–	–	0.8	μs
Switching times inductive load (see Figs 10 and 13)						
t_s	storage time	$I_{Con} = 4\text{ A}$; $I_{Bon} = 800\text{ mA}$; $V_{CL} = 250\text{ V}$	–	1.6	2.5	μs
t_f	fall time	$I_{Con} = 4\text{ A}$; $I_{Bon} = 800\text{ mA}$; $V_{CL} = 250\text{ V}$	–	150	400	ns

Note

1. Measured with a half-sinewave voltage (curve tracer).

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$T_{mb} = 25\ ^\circ C$.

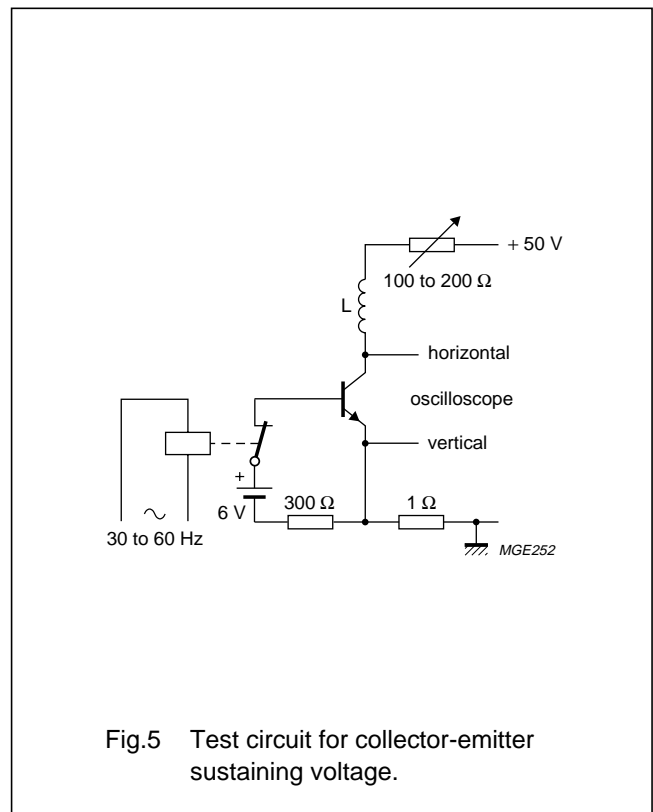
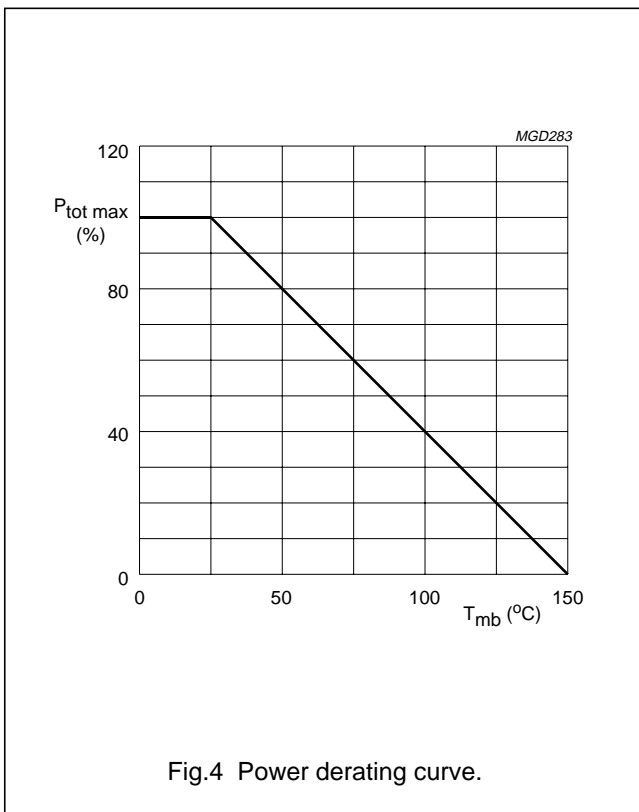
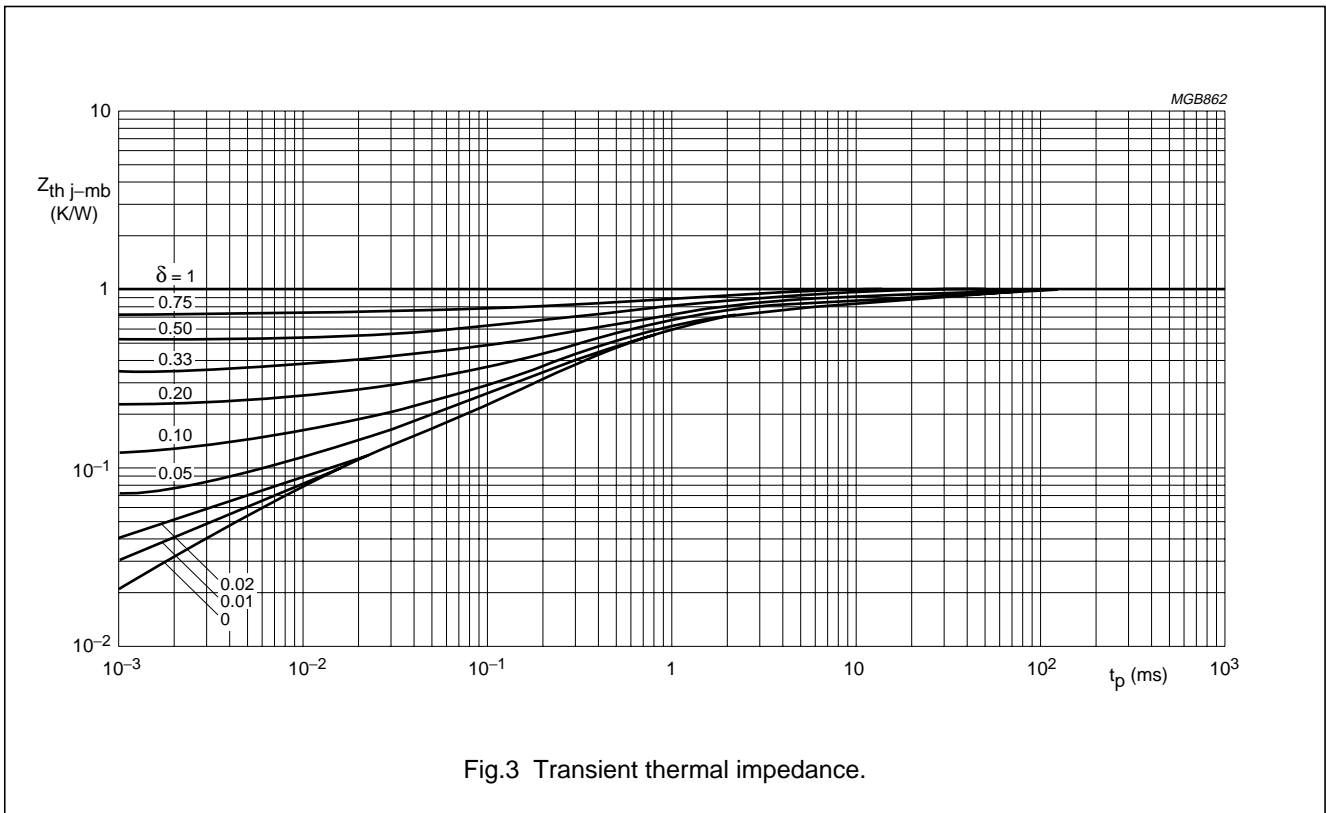
I - Region of permissible DC operation.

II - Permissible extension for repetitive pulse operation.

Fig.2 Forward bias SOAR.

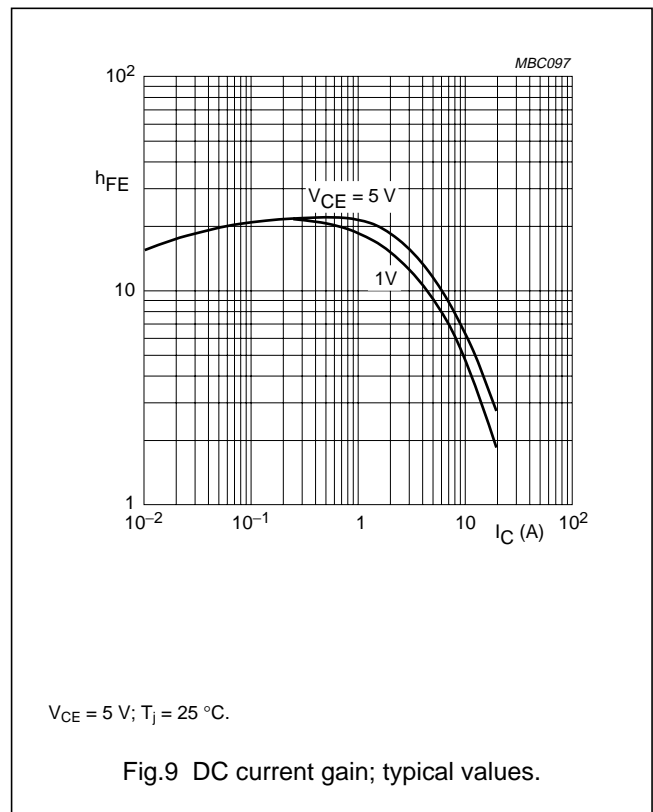
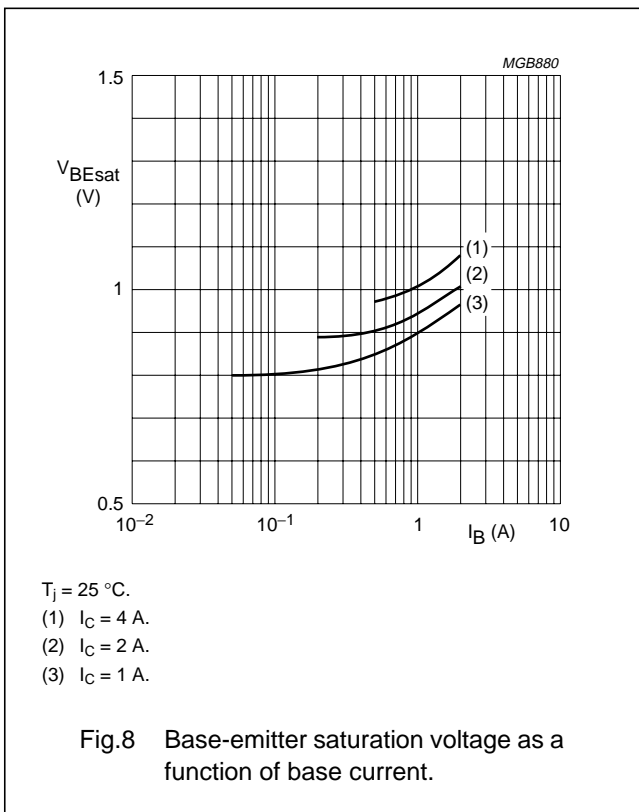
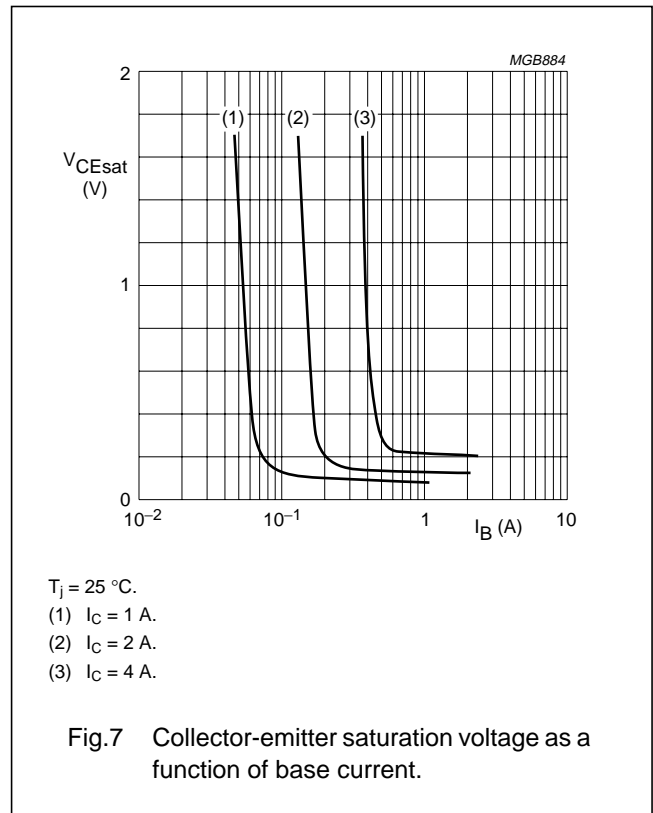
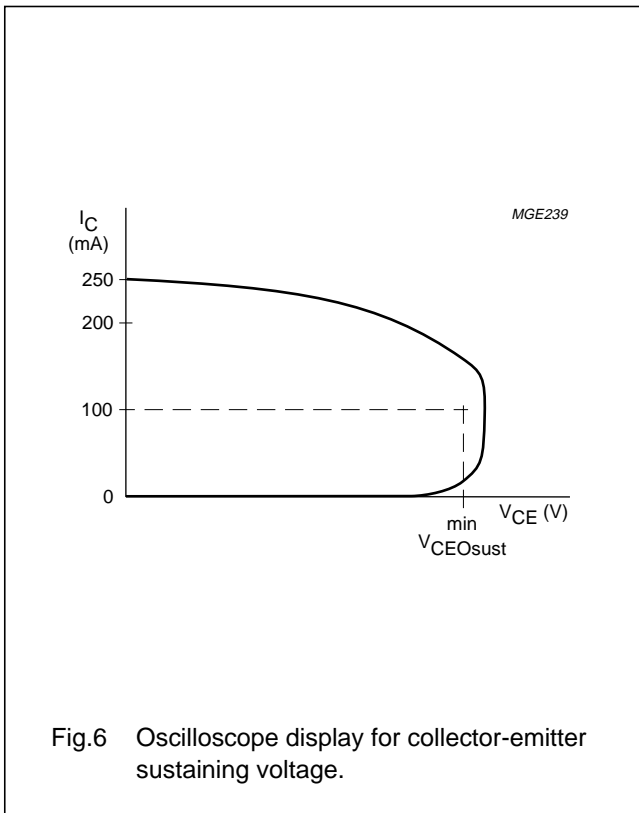
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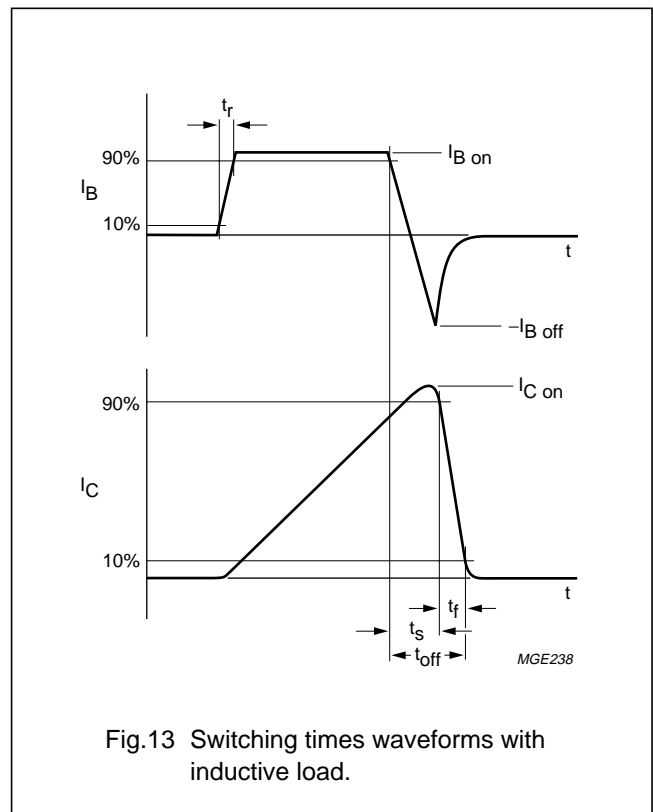
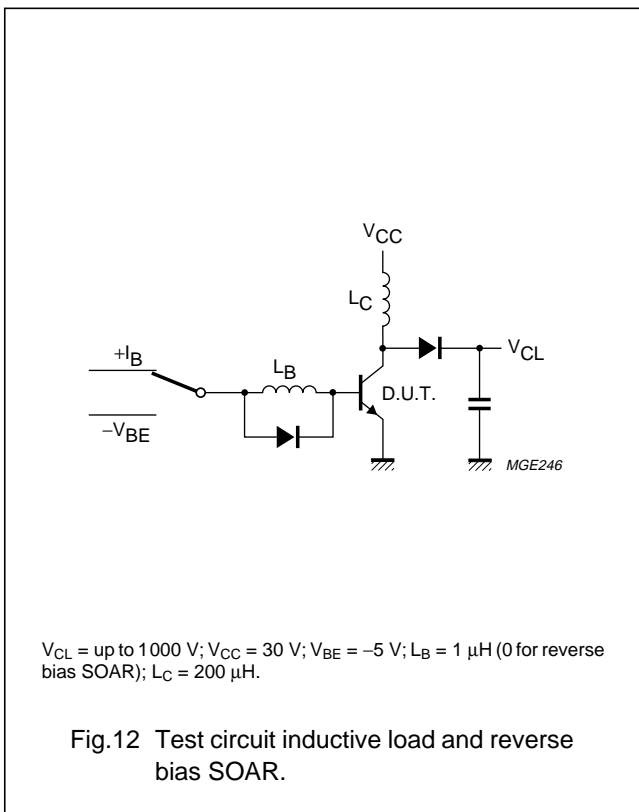
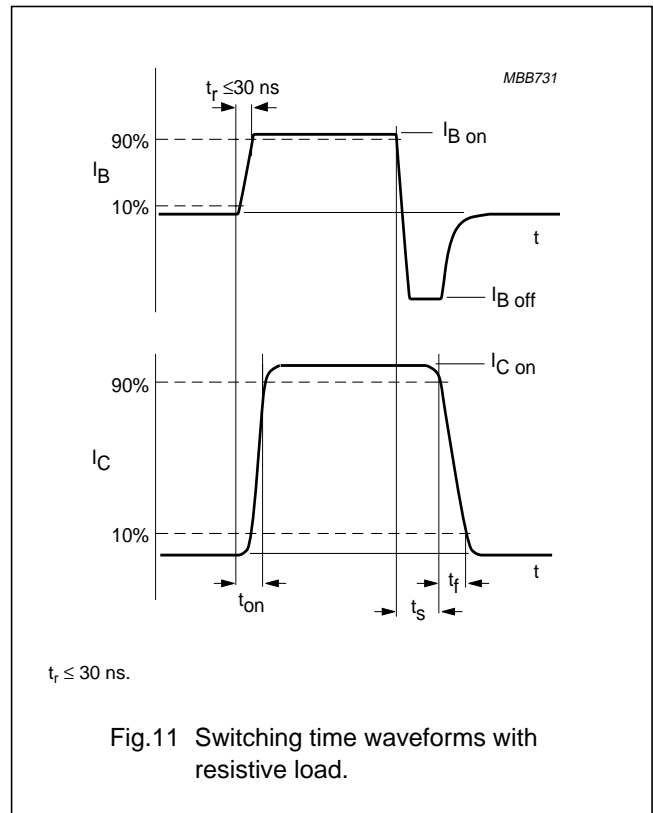
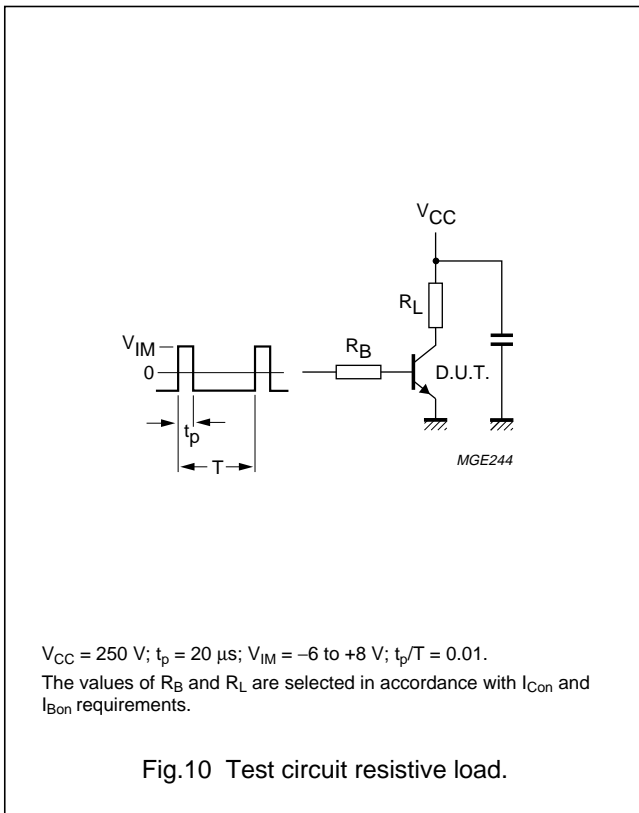
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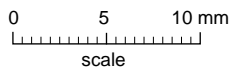
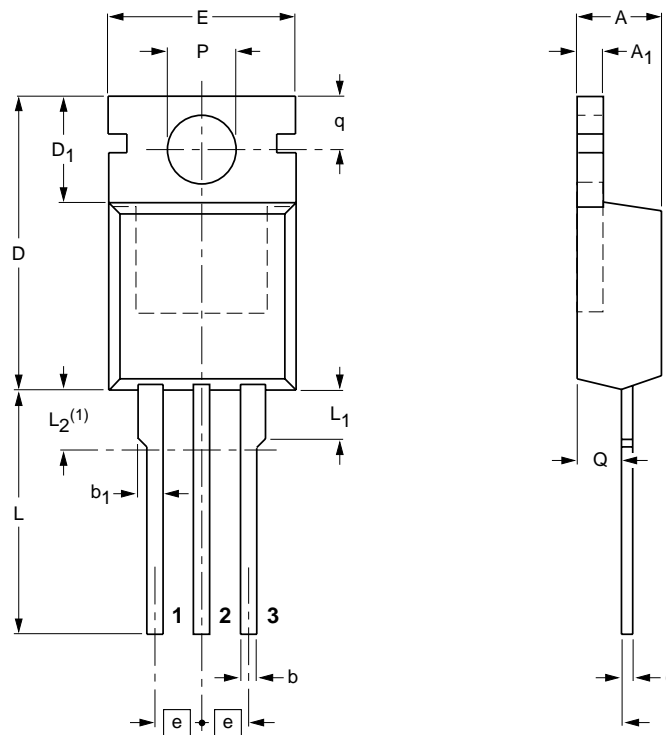
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PACKAGE OUTLINE

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁	c	D	D ₁	E	e	L	L ₁	L ₂ ⁽¹⁾ max.	P	q	Q
mm	4.5 4.1	1.39 1.27	0.9 0.7	1.3 1.0	0.7 0.4	15.8 15.2	6.4 5.9	10.3 9.7	2.54	15.0 13.5	3.30 2.79	3.0	3.8 3.6	3.0 2.7	2.6 2.2

Note

1. Terminals in this zone are not tinned.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT78		TO-220AB				97-06-11

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DEFINITIONS

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Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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NOTES

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Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113,
Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213,
Tel. +43 1 60 101 1248, Fax. +43 1 60 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,
220050 MINSK, Tel. +375 172 20 0733, Fax. +375 172 20 0773

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Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,
51 James Bourchier Blvd., 1407 SOFIA,
Tel. +359 2 68 9211, Fax. +359 2 68 9102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,
Tel. +1 800 234 7381, Fax. +1 800 943 0087

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,
Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America

Czech Republic: see Austria

Denmark: Sydhavnsgade 23, 1780 COPENHAGEN V,
Tel. +45 33 29 3333, Fax. +45 33 29 3905

Finland: Sinikalliontie 3, FIN-02630 ESPOO,
Tel. +358 9 615 800, Fax. +358 9 6158 0920

France: 51 Rue Carnot, BP317, 92156 SURESNES Cedex,
Tel. +33 1 4099 6161, Fax. +33 1 4099 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,
Tel. +49 40 2353 60, Fax. +49 40 2353 6300

Hungary: see Austria

India: Philips INDIA Ltd, Band Box Building, 2nd floor,
254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,
Tel. +91 22 493 8541, Fax. +91 22 493 0966

Indonesia: PT Philips Development Corporation, Semiconductors Division,
Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510,
Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,
20124 MILANO, Tel. +39 02 67 52 2531, Fax. +39 02 67 52 2557

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku,
TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5057

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,
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Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,
Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,
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Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
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Norway: Box 1, Manglerud 0612, OSLO,
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Philippines: Philips Semiconductors Philippines Inc.,
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Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Ul. Lukiska 10, PL 04-123 WARSZAWA,
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Portugal: see Spain

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Russia: Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,
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04547-130 SÃO PAULO, SP, Brazil,
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Spain: Balmes 22, 08007 BARCELONA,
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Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,
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Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH,
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Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,
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United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,
MIDDLESEX UB3 5BX, Tel. +44 208 730 5000, Fax. +44 208 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,
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Uruguay: see South America

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